(b) Amendments to the Claims

The following is a complete listing of the claims in this application, reflects all changes currently being made to the claims, and replaces all earlier versions and all earlier listings of the claims:

1. (Currently Amended) A method for producing a crystalline film by melting and resolidifying a film comprising the steps of:

preparing a film having a specific amorphous region obtained by a step of forming a film in which a specific amorphous region and a peripheral amorphous region continuous to a periphery of the specific amorphous region and different in thickness from the specific amorphous region co-exist[[;]], the film having a thickness larger in the specific amorphous region than in the peripheral amorphous region;

melting at least a part of the film so that a single crystal grain or a single cluster remains unmelted in the specific amorphous region; and

resolidifying the film so that crystal growth occurs in a direction from the specific amorphous region toward the peripheral amorphous region.

Claim 2. (Cancelled).

3. (Previously Presented) The method according to claim 1, wherein the step of preparing a film includes a step of forming a concave portion on a surface of a substrate on which the film is provided.

Claim 4. (Cancelled).

- 5. (Previously Presented) The method according to claim 1, wherein, at a maximum melting state of the film in the melting-resolidification process, a single crystal grain or single crystalline cluster remains unmelted in the specific amorphous region while the peripheral amorphous region thereof is completely melted.
- 6. (Previously Presented) The method according to claim 5, wherein a ratio of a dimension to a thickness of the specific amorphous region is larger, when a crystal growth of the single crystal grain or the single crystalline cluster existing in the specific amorphous region executes a crystal growth in a resolidification step, than a ratio of a growth velocity in a planar direction to a growth velocity in a direction of film thickness in the specific amorphous region.
- 7. (Previously Presented) The method according to claim 5, wherein a ratio of a dimension to a thickness of the specific amorphous region is, when a crystal growth of the single crystal grain or the single crystalline cluster existing in the specific amorphous region executes a crystal growth in a resolidification step, within such a range that a growth front in a direction of film thickness reaches a surface of the film before a growth front in a planar direction of the film reaches a periphery of the specific amorphous region.
- 8. (Previously Presented) The method according to claim 5, wherein a ratio of a dimension of the specific amorphous region to a thickness difference between the specific

amorphous region and the peripheral amorphous region is larger, when a crystal growth of the single crystal grain or single crystalline cluster existing in the specific amorphous region executes a crystal growth in a resolidification step, than a ratio of a growth velocity in a planar direction to a growth velocity in a direction of film thickness in the specific amorphous region.

- 9. (Previously Amended) The method according to claim 5, wherein a ratio of a dimension of the specific region to a thickness difference between the specific amorphous region and the peripheral amorphous region is larger, when a crystal growth of the single crystal grain or the single crystalline cluster existing in the specific amorphous region executes a crystal growth in a resolidification step, within such a range that a growth front in a direction of film thickness reaches a surface of the film before a growth front in a planar direction of the film reaches a periphery of the specific amorphous region.
 - 10. 30. (Cancelled).
- 31. (Previously Presented) The method according to claim 1, wherein a spatial position of at least a part of crystal grains having a continuous crystalline structure in the crystalline film is determined by a spatial position of the specific amorphous region.
- 32. (Previously Presented) An element utilizing a crystalline film obtained by a producing method according to claim 1, wherein a spatial position of at least a part of crystal grains having a continuous crystalline structure in the crystalline film is determined by a spatial

position of the specific amorphous region, and a crystal grain having the determined spatial position is utilized as an active area.

- 33. (Original) The element according to claim 32, wherein an active area is formed inside a single crystal grain of the crystalline film.
- 34. (Original) A circuit including a plurality of the element according to claim32, and a wiring between the elements.
- 35. (Currently Amended) The method according to claim 1, characterized in that, by defining a melting point of a bulk crystal as Tc and a supercooling degree causing a spontaneous nucleation from a molten phase as Δ Tc in a melting-resolidification process of the film, the specific amorphous regions are provided with such an interval a predetermined interval such that a portion positioned between the specific amorphous regions of the predetermined interval reaches a temperature equal to or higher than Tc Δ Tc at a time when an unsolidified region reaches a supercooling degree of DTc at the resolidification of the film.
- 36. (Currently Amended) The method according to claim 35, wherein the specific amorphous regions are provided with such an interval a predetermined interval such that a portion where a region, in the vicinity of a growth front of a crystal grain growing from a specific amorphous region and having a higher temperature than in a periphery, overlaps with a region, in the vicinity of a growth front of a crystal grain growing from another specific

amorphous region and having a higher temperature than in a periphery, has a temperature equal to or higher than Tc - ΔTc .

- 37. (Currently Amended) The method according to claim 36, wherein the specific amorphous regions are provided with such an interval a predetermined interval such that growth fronts of crystal grains growing from two specific amorphous regions mutually contact before a time when a portion where a high-temperature region, in the vicinity of a growth front of a crystal grain growing from a specific amorphous region, overlaps with a high-temperature region, in the vicinity of a growth front of a crystal grain growing from another specific region, reaches a temperature equal to or lower than $Tc \Delta Tc$.
- 38. (Original) The method according to claim 1, characterized, in a melting-resolidification process of a film, in melting the film with plural heating means and resolidifying the film.
- 39. (Original) The method according to claim 38, wherein at least one of the plural heating means is heating means having a constant heating intensity without a change with time, in a melting process of the film.
- 40. (Original) The method according to claim 39, wherein the heating means having a constant heating intensity is a heat conduction from a substrate, an irradiation with a continuously oscillated laser light, or a current-supply heating of the film.

- 41. (Original) The method according to claim 38, wherein at least one of the plural heating means is heating means having a heating intensity changing with time, in a melting process of the film.
- 42. (Original) The method according to claim 41, wherein the heating means having a heating intensity changing with time is a pulsed laser irradiating the film with two pulses of different intensities with a time difference.
- 43. (Original) The method according to claim 38, wherein the plural heating means includes heating means having a constant heating intensity without a change with time in a melting process of the film, and heating means having a heating intensity changing with time in a melting process of the film.
- 44. (Original) The method according to claim 38, wherein the plural heating means includes heating means which heats the film to a temperature not exceeding a melting point, and heating means for heating the temperature-elevated film thereby melting the film.
- 45. (Original) The method according to claim 1, characterized in including a step of giving a heat not changing with time to the film thereby heating the film to a temperature not exceeding a melting point, a step of giving a heat changing with time thereby heating and melting the temperature-elevated film, and a step of resolidifying the film.

46. - 48. (Cancelled).